

TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA2030FNG

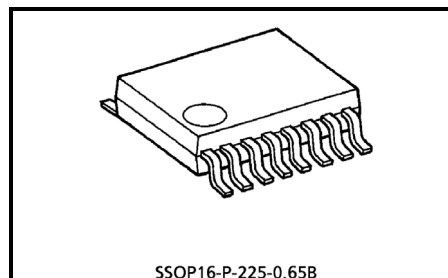
TV / FM System F / E (1.5V USE)

The TA2030FNG is a TV / FM system front end IC, which is developed for headphone radio in 1.5V use.

It is built in FM F / E and TV F / E (japanese VHF band).

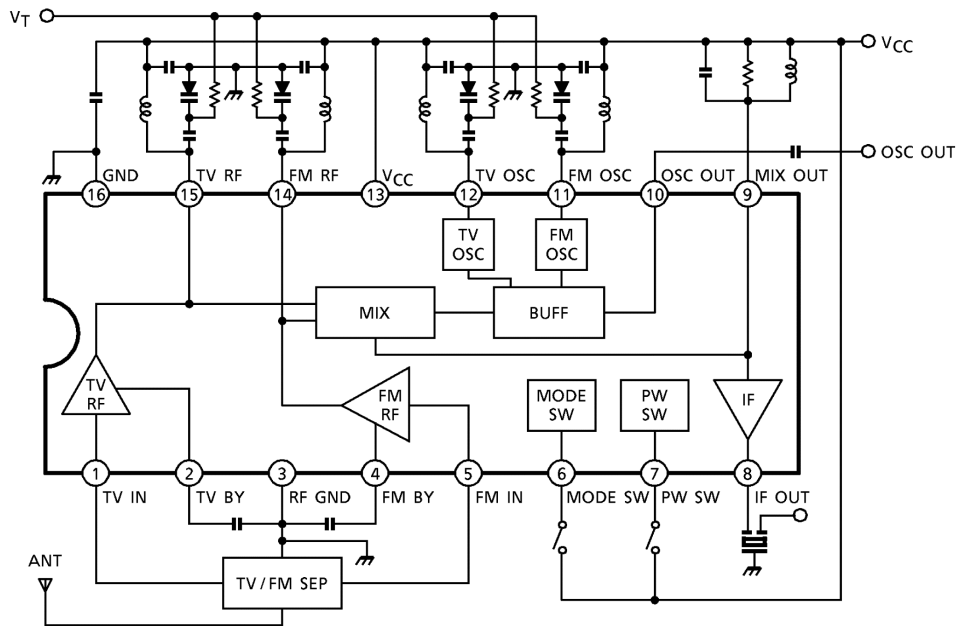
Features

- Built-in FM F / E and TV F / E
FM mode: 75~109MHz
TV mode: 175~225MHz
- Suitable for combination with digital tuning system.
- Built-in power switch
- Built-in FM / TV switch
- Built-in IF amplifier
- Built-in OSC buffer circuit
- Improved inter-modulation characteristics by double balanced type mixer circuit.
- Supply current ($V_{CC} = 1.2V$, $T_a = 25^{\circ}C$)
FM mode: $I_{CC} = 4.4mA$ (typ.)
TV mode: $I_{CC} = 6.3mA$ (typ.)
- Operating supply voltage range ($T_a = 25^{\circ}C$)
 $V_{CC (opr)} = 0.95\sim 4V$



Weight: 0.09g (typ.)

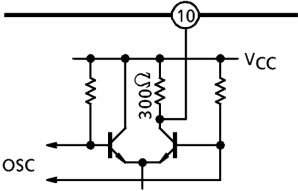
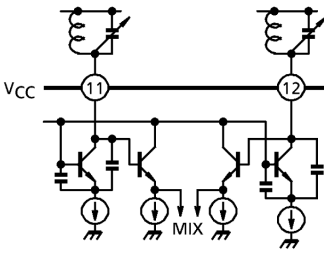
Block Diagram



Terminal Explanation

Terminal Voltage: Typical Terminal Voltage at no Signal with Test Circuit. ($V_{CC} = 1.2V$, $T_a = 25^\circ C$)

Terminal No.	Terminal Name	Function	Internal Circuit	Terminal Voltage(V)	
				FM	TV
1	TV IN	Input of TV RF signal (common-base type)		—	0.1
2	TV BY	By-pass terminal of TV RF and MIX (radiation is lightened by connected capacitor.)		—	0.7
15	TV RF	TV RF tuning circuit is connected.		1.2	1.2
3	RF GND	—	—	0	0
4	FM BY	By-pass terminal of FM RF and MIX (radiation is lightened by connected capacitor.)		0.7	—
5	FM IN	Input of FM RF signal (common-base type)		0.1	—
14	FM RF	FM RF tuning circuit is connected.		1.2	1.2
6	MODE SW	Mode switch V_{CC} : TV mode OPEN / GND: FM mode		0	1.2
7	PW SW	Power switch V_{CC} : Power on OPEN / GND: Power off		1.2	1.2
8	IF OUT	Output of TV / FM IF signal. Output impedance 330Ω (typ.)		1.1	1.1
9	MIX OUT	MIX coil is connected.		1.2	1.2

Terminal No.	Terminal Name	Function	Internal Circuit	Terminal Voltage(V)	
				FM	TV
10	OSC OUT	Output of OSC buffer circuit.		1.1	1.1
11	FM OSC	FM OSC tank circuit is connected. (colpitts type oscillator)		1.2	1.2
12	TV OSC	TV OSC tank circuit is connected. (colpitts type oscillator)		1.2	1.2
13	V _{CC}	V _{CC}		1.2	1.2
16	GND	GND(except RF part)		0	0

Application Note

1. PW SW

It is necessary to connect an external pull-down resistor with the terminal PW SW (pin(7)), in case that this IC is turned on due to external noise etc.

2. MODE SW

It is necessary to connect an external pull-down resistor with the terminal MODE SW (pin(6)), in case that this IC doesn't operate normally due to external noise etc.

3. RF GND

This IC has two GND terminals (pin(3): RF GND, pin(16): GND). External parts shown in below should be connected with RF GND (pin(3)), and other parts should be connected with GND (pin(16)).

- By-pass capacitor at pin(14) (FM RF) and pin(15) (TV RF)
- By-pass capacitor at pin(4) (FM BY) and pin(2) (TV BY)

The pattern diagram of capacitor connected with pin(2) and pin(4) should be shortly, because RF circuit and MIX circuit operate on the voltage of pin(2) or pin(4).

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5	V
Power dissipation (Note)	P _D	400	mW
Operating temperature	T _{opr}	-25~75	°C
Storage temperature	T _{stg}	-55~150	

Note: Derated above Ta = 25°C in the proportion of 3.2mW / °C

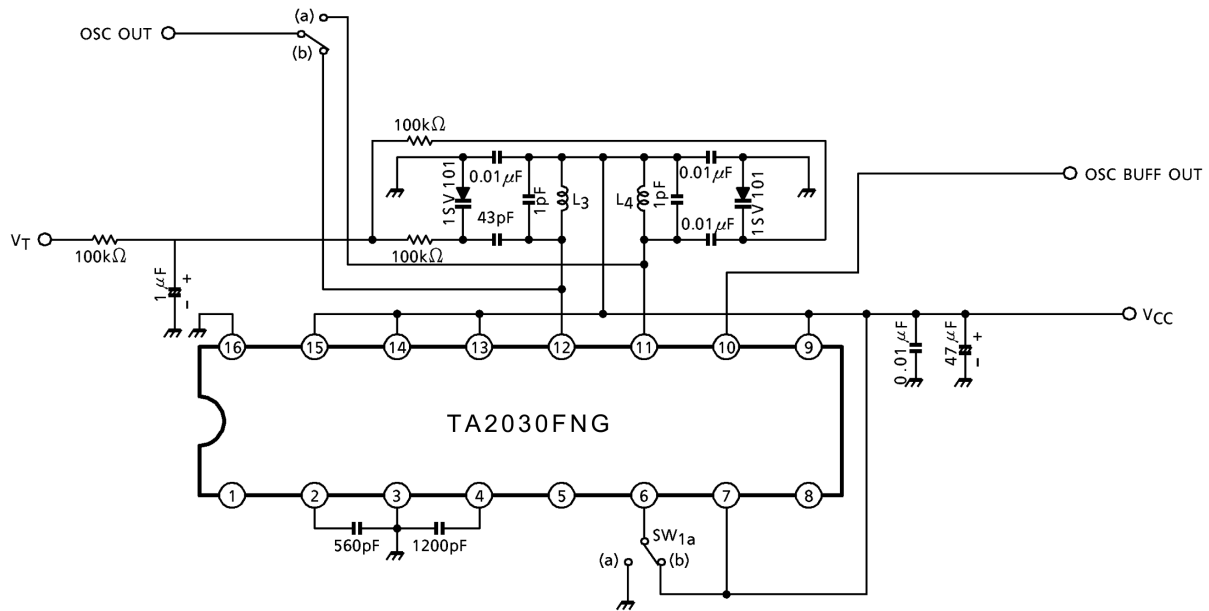
Electrical Characteristics

Unless Otherwise Specified, V_{CC} = 1.2V, Ta = 25°C, f_{FM} = 92MHz, f_{TV} = 200MHz
 $\Delta f = \pm 22.5\text{kHz}$, f_m = 1kHz, SW₂ : b

Characteristic		Symbol	Test Cir- cuit	SW ₁	Test Condition		Min.	Typ.	Max.	Unit
Supply current		I _{CC1}	1	a	V _{in} < -20bBμV EMF	IC OFF, SW ₂ : a	—	0.1	5	μA
		FM mode				—	4.4	6.6	mA	
		I _{CC3}		b		TV mode	—	6.3		9.5
FM	Conversion gain	G _{C1}	2	a	V _{in} = 65dBμV EMF		29	33	—	dB
	Local oscillator voltage	V _{OSC1}	3		f _{osc} = 65MHz	—	360	—	mV _{rms}	
	OSC buffer output voltage	V _{BUF1}				—	50	—		
	Local oscillator stop voltage	V _{STP1}				—	0.89	0.95	V	
TV	Conversion gain	G _{C2}	2	b	V _{in} = 65dBμV EMF		25	29	—	dB
	Local oscillator voltage	V _{OSC2}	3		f _{osc} = 165MHz	—	180	—	mV _{rms}	
	OSC buffer output voltage	V _{BUF2}				—	22	—		
	Local oscillator stop voltage	V _{STP2}				—	0.86	0.95	V	
Power on current		I ₇	1	a	V _{CC} = 0.95V, V ₂ ≤ 0.2 V SW ₂ : d V ₄ ≥ 0.4 V		5	—	—	μA
Power off voltage		V ₇		a	V _{CC} = 0.95V, V ₂ ≤ 0.2 V SW ₂ : c V ₄ ≤ 0.2 V		0	—	0.3	V
TV mode on current		I ₆		d	V _{CC} = 0.95V, V ₂ ≥ 0.4 V V ₄ ≤ 0.2 V		5	—	—	μA
FM mode on voltage		V ₆		c	V _{CC} = 0.95V, V ₂ ≤ 0.2 V V ₄ ≥ 0.4 V		0	—	0.3	V

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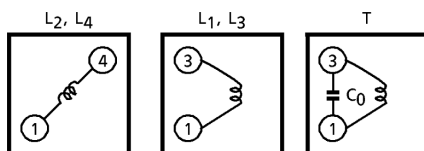
Test Circuit 3

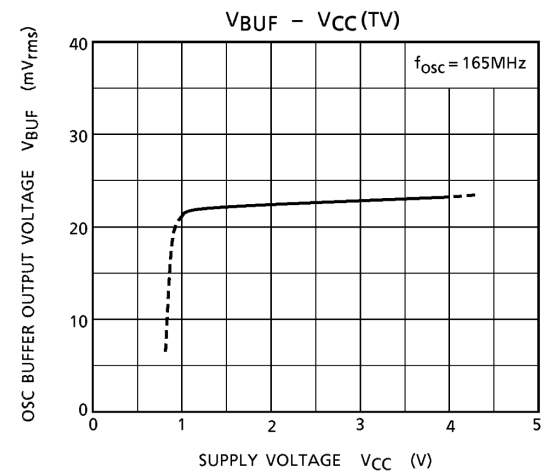
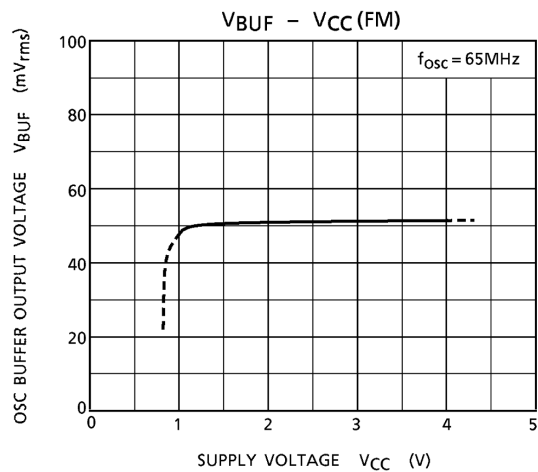
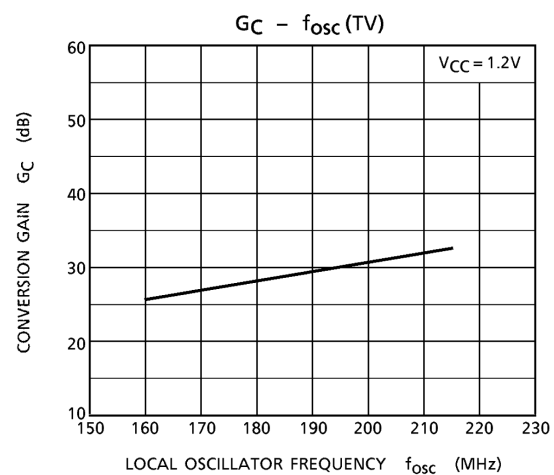
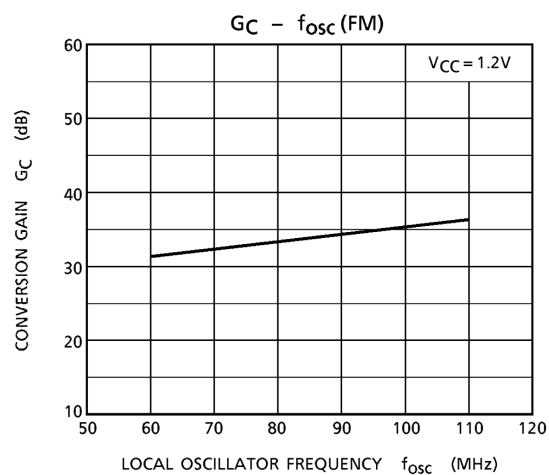
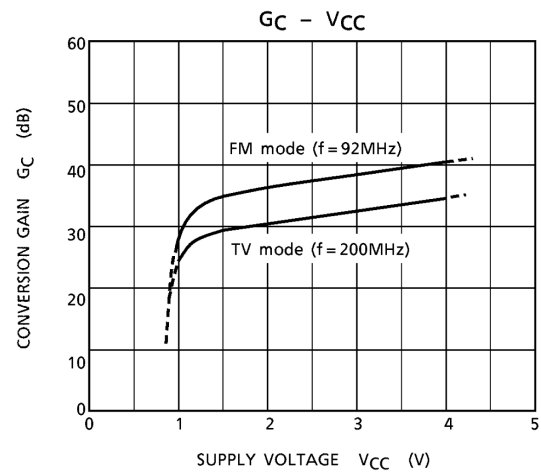
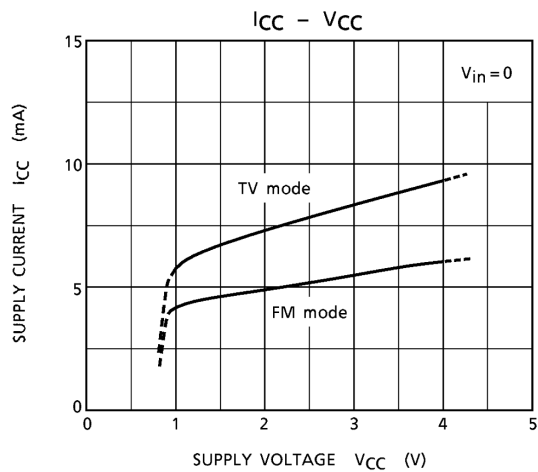


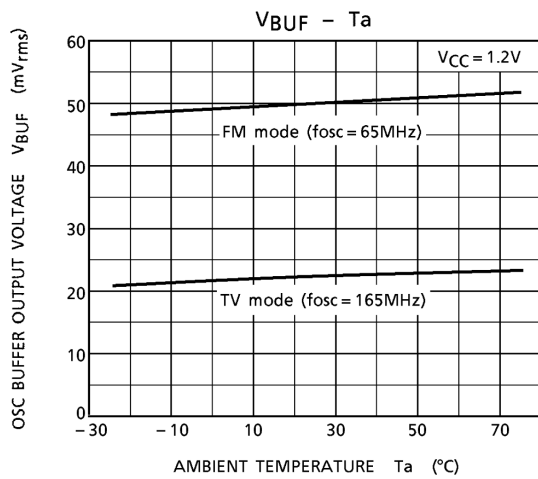
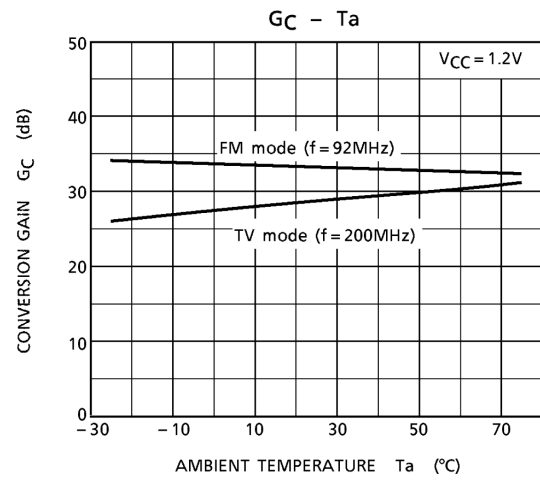
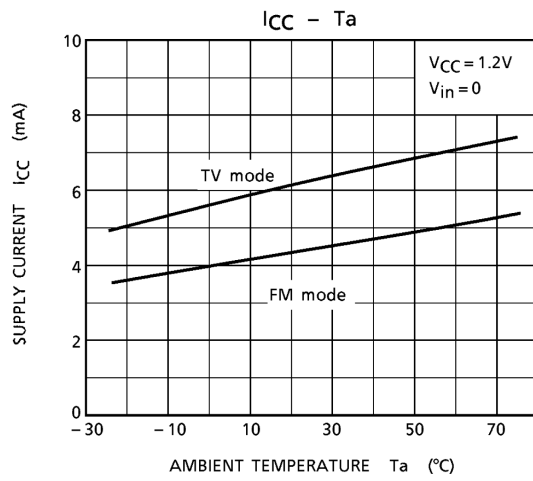
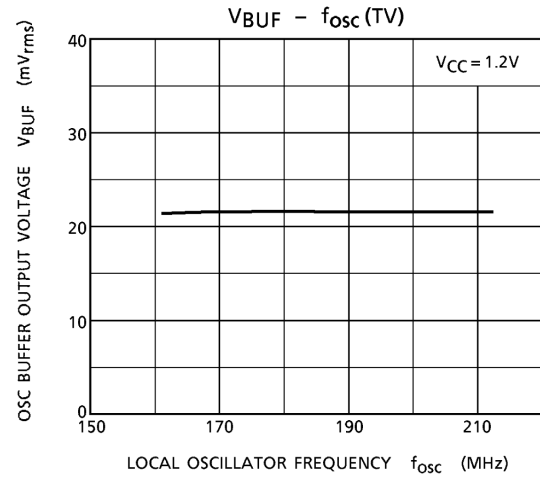
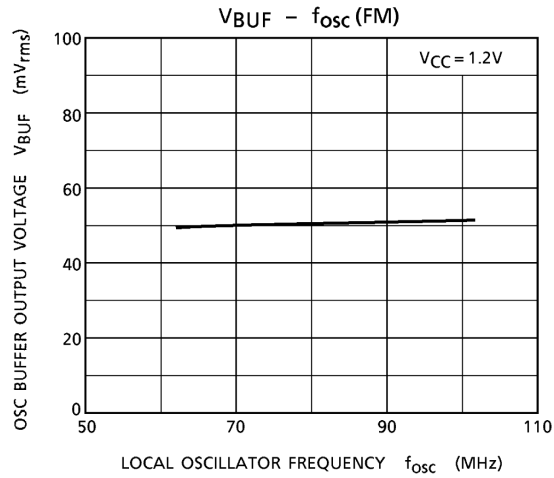
Coil Data (test circuit)

Coil No.	Test Freq.	C ₀ (pF)	Q ₀	Turns		Wire (mmφ)	Reference
				1-3	1-4		
L ₁ TV RF	100MHz	—	55	1 1/4	—	0.5UEW	(S) 0258-250
L ₂ FM RF	100MHz	—	90	—	3 1/2	0.5UEW	(S) 0258-238
L ₃ TV OSC	100MHz	—	55	1 1/4	—	0.5UEW	(S) 0258-250
L ₄ FM OSC	100MHz	—	90	—	3 1/2	0.5UEW	(S) 0258-238
T FM IFT	10.7MHz	82	45	18	—	0.09UEW	(S) 4162-083A

(S) : Sumida electric CO., LTD



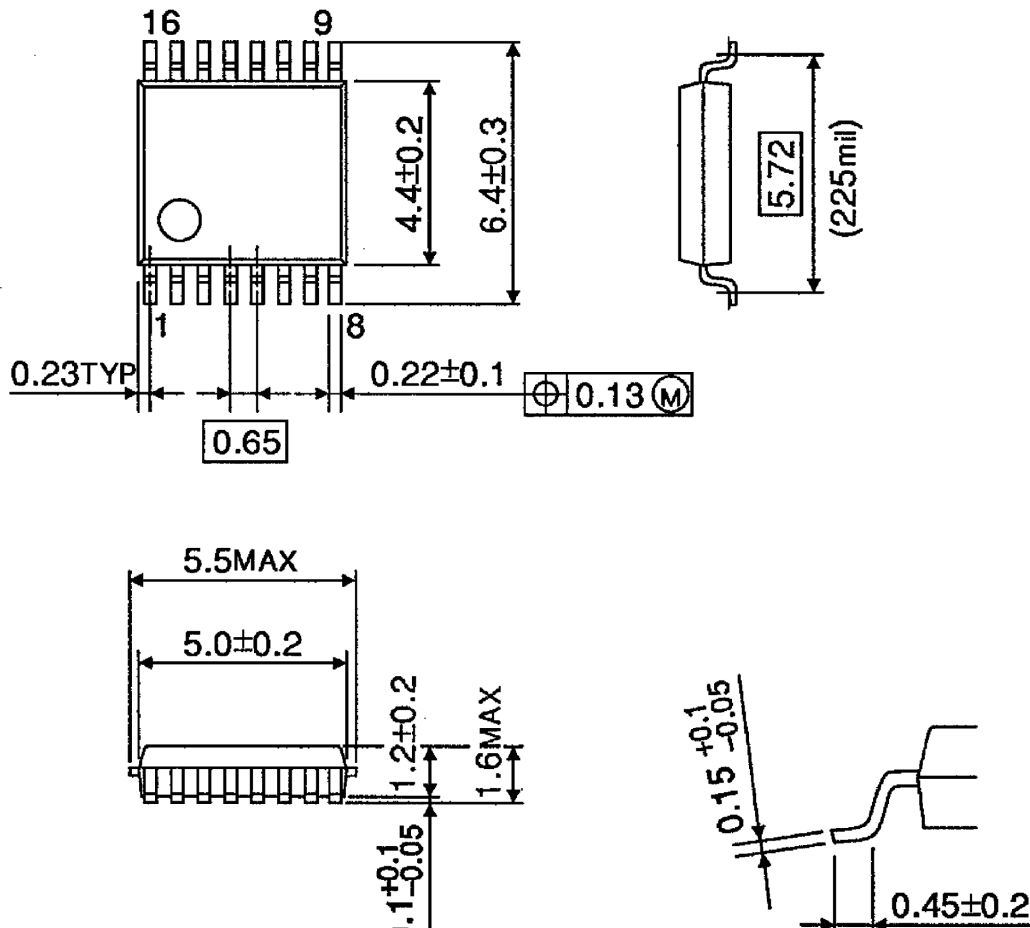




Package Dimensions

SSOP16-P-225-0.65B

Unit : mm



Weight: 0.09g (typ.)

About solderability, following conditions were confirmed

- Solderability

- (1) Use of Sn-63Pb solder Bath

- solder bath temperature = 230°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux

- (2) Use of Sn-3.0Ag-0.5Cu solder Bath

- solder bath temperature = 245°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux

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